

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

Inventor(s): MIYASHITA et al.

Filed: Herewith

Title: SEMICONDUCTOR DEVICE COMPRISING METAL SILICIDE FILMS FORMED TO COVER GATE ELECTRODE AND SOURCE-DRAIN DIFFUSION LAYERS AND METHOD OF MANUFACTURING THE SAME

July 30, 2001

PRELIMINARY AMENDMENT

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

Please amend this application as follows:


IN THE SPECIFICATION:

At the top of the first page, just under the title, insert:

1. ☒--This is a ☐ Continuation-In-Part ☒ Divisional
☐ Continuation ☐ Substitute Application (MPEP 201.09) of
1(a) ☐ National Application No. 09/164,343 filed October 1, 1998.
1(b) ☐ International Application No. PCT/___/
filed ___ which designated the U.S.--
2. ☐--This application claims the benefit of U.S. Provisional Application No. 60/___, filed ___.--

Respectfully submitted,

PILLSBURY WINTHROP LLP
Intellectual Property Group

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